

# Design and Fabrication of PERC-Like CdTe Solar Cells Using Micropatterned Al<sub>2</sub>O<sub>3</sub> Layer

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**Abstract**—Recent studies have investigated novel strategies to further improve the limited  $V_{oc}$  of CdTe solar cells via increased carrier lifetime and doping density of CdTe thin films. Among various metal oxides, aluminum oxide (Al<sub>2</sub>O<sub>3</sub>) is a promising passivation candidate, where the negatively charged Al<sub>2</sub>O<sub>3</sub> layer repels the minority carrier in CdTe and Al<sub>2</sub>O<sub>3</sub> provides a chemically passivating interface, increasing the carrier lifetime. Despite the continuing efforts, an optimized back-contact architecture to improve the  $V_{oc}$  while maintaining high  $J_{sc}$  and  $FF$  is still under development. In this work, we report the design, fabrication, and characterization of PERC-like CdTe solar cells, where an Al<sub>2</sub>O<sub>3</sub> passivation layer is patterned using laser-beam lithography. Our process enables reproducible patterning on a rough surface CdTe while maintaining the size of the array in the design. Analysis of CdTe PERC devices (As-doped) shows a notably different  $V_{oc}$  trend compared to  $FF$  and  $J_{sc}$ , independent of the patterned array structures used in this study. The subsurface electronic structure of CdTe and the interplay between carrier selectivity and collection of the patterned Al<sub>2</sub>O<sub>3</sub> could be responsible for the observed PV characteristics.

## I. INTRODUCTION

Thin-film CdTe solar cells are a competitive photovoltaic (PV) technology that can meet the rapidly growing societal demand for energy owing to cost-effective manufacturing and relatively short energy payback time [1, 2]. At a record efficiency of 22.1 %, significant attention has been devoted to further improving the power conversion efficiencies of CdTe-based solar cells [3-5]. An optimized front contact that leads the  $J_{sc}$  over 31 mA/cm<sup>2</sup> and a fill factor (FF) above 79 % were reported [6, 7]. An open-circuit voltage ( $V_{oc}$ ) over 1 V was achieved with As-doped CdTe single crystals. Despite the continuing efforts, high  $V_{oc}$  (> 1 V) has not yet been observed in thin-film polycrystalline CdTe PVs. The underlying physical mechanisms responsible for the  $V_{oc}$  loss are not presently well understood.

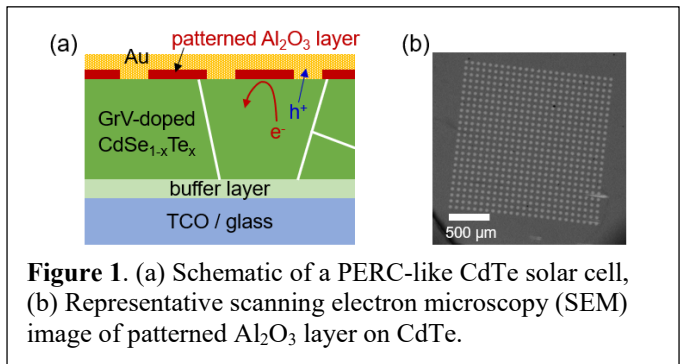
Recent studies have demonstrated novel device architectures and passivation strategies to enhance the  $V_{oc}$  via increasing carrier lifetime and doping density of CdTe thin films. Among various metal oxides, Al<sub>2</sub>O<sub>3</sub> is a promising passivation candidate, where the negatively charged Al<sub>2</sub>O<sub>3</sub> layer (fixed charge density of 10<sup>12</sup> ~ 10<sup>13</sup> cm<sup>-2</sup>) could repel the minority carrier (electrons) in CdTe, increasing the carrier lifetime [7, 8]. Previous studies also suggested that Al<sub>2</sub>O<sub>3</sub> could passivate the CdTe surface via chemical reactions during the fabrication processes. This configuration is similar to a passivated emitter and rear contact (PERC) design, frequently used in Si

photovoltaic (PV) technology [9, 10]. An improved  $V_{oc}$  was reported with a conformal Al<sub>2</sub>O<sub>3</sub> (< 5 nm) on CdTe, yet the  $J_{sc}$  and FF suffer from the tunneling barrier [11-18]. On the other hand, Kephart and co-workers used a 20 nm-thick Al<sub>2</sub>O<sub>3</sub> with micropatterning. A remarkably high lifetime ( $\tau_2 > 400$  ns) was measured for double heterostructures, but no consistent improvement of  $V_{oc}$  was observed for the Cu-doped CdTe solar cells [11].

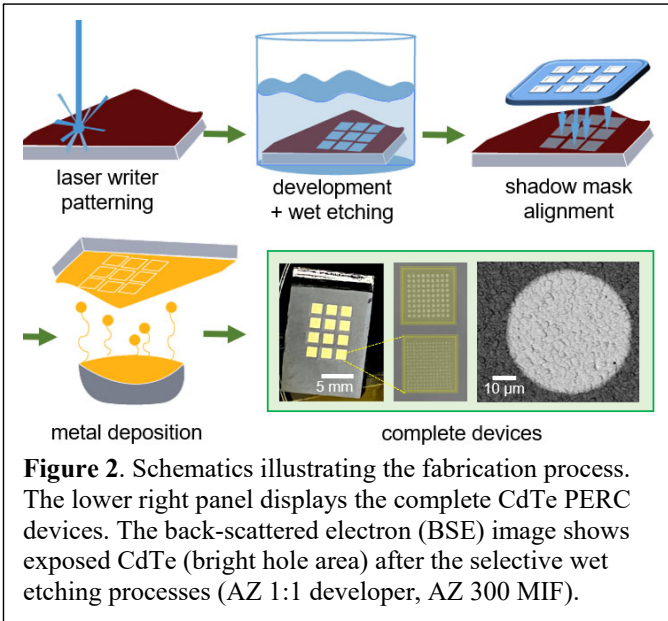
This work reports the design and fabrication of PERC-like CdTe solar cells (CdTe PERC), where the Al<sub>2</sub>O<sub>3</sub> passivation layer is patterned via laser-beam lithography. We optimize the beam dose to polymerize the photoresist on a rough surface CdTe while maintaining the size of the array in the design. We measure the dark and light  $I$ - $V$ s of As-doped CdSeTe PERC having different hole diameters and pitches (i.e., the distance between adjacent holes). Quantitative analysis shows the impact of Al<sub>2</sub>O<sub>3</sub> patterns on  $V_{oc}$  is notably different from other device parameters of  $J_0$ ,  $J_{sc}$ , and  $FF$ . We discuss a similar  $V_{oc}$  trend observed after annealing (70°C for 2.5 hours) of the complete CdTe PERC. Our results indicate the electrically-active Al<sub>2</sub>O<sub>3</sub> patterns, in conjunction with the defect chemistry in CdTe bulk, could play an essential role in determining the  $V_{oc}$  of advanced CdTe-based solar cells.

## II. EXPERIMENT

Figure 1(a) displays a schematic of a CdTe PERC device consisting of a thin-film CdTe solar cell and a patterned Al<sub>2</sub>O<sub>3</sub>. The As-doped CdSeTe/CdTe absorber layer was synthesized on a stack of buffer/TCO [transparent conductive oxide]/glass substrate. A scanning electron microscopy (SEM) image shows a representative Al<sub>2</sub>O<sub>3</sub> hole array on CdTe fabricated in this work (Figure 1b). The same-size individual holes are uniformly



**Figure 1.** (a) Schematic of a PERC-like CdTe solar cell, (b) Representative scanning electron microscopy (SEM) image of patterned Al<sub>2</sub>O<sub>3</sub> layer on CdTe.



distributed in a square pattern across the entire device. This study used three different hole sizes (10  $\mu\text{m}$ , 20  $\mu\text{m}$ , and 40  $\mu\text{m}$ ). The distance between the adjacent holes ranges from 10  $\mu\text{m}$  to 320  $\mu\text{m}$ , introducing different sizes of the exposed CdTe area to metal contact.

Figure 2 illustrates the fabrication procedures to produce patterned  $\text{Al}_2\text{O}_3$  back contacts. As-doped CdSeTe/CdTe solar cells were obtained from First Solar that was coated with a 20 nm  $\text{Al}_2\text{O}_3$  layer. The samples were cleaned with acetone and isopropyl alcohol (IPA), and blown dry with nitrogen ( $\text{N}_2$ ). The samples were baked on a hot plate at 100°C for 60 seconds and cooled down before spin coating of photoresist. A thin layer of positive photoresist (Shipley1813) was coated on the sample at a spin speed of 3,000 rpm (revolution per minute) for 60 seconds, followed by soft baking for another 60 seconds on the hot plate at 100°C. A laser writer (Heidelberg  $\mu\text{PG}$  101) was used to pattern the hole array design (L-Edit) on the photoresist-coated  $\text{Al}_2\text{O}_3$  on CdTe.

We performed a series of control experiments to optimize the laser dose that could polymerize the photoresist on a rough surface CdTe while maintaining the size of the array of the design [19]. We found a relatively high beam energy (an effective dose of 13.5 mW) is needed for CdTe compared to traditional Si flat samples (10 mW). The photoresist was developed in a solution (AZ Developer 1:1) for 60 seconds and soaked in DI water. We used another solution (AZ 300 MIF) to selectively etch the exposed  $\text{Al}_2\text{O}_3$  on CdTe after the photoresist development. This chemical contains a small amount of tetramethyl ammonium hydroxide (< 3 % TMAH), which has a faster etch rate for  $\text{Al}_2\text{O}_3$  than photoresist. The  $\text{Al}_2\text{O}_3$  etching was conducted for 20 minutes, followed by the photoresist removal and cleaning using acetone, IPA, deionized water, and  $\text{N}_2$ -blown dried.

The metal contact for each device was designed to be 2 mm  $\times$  2 mm in size. We fabricated a shadow mask using a stainless-

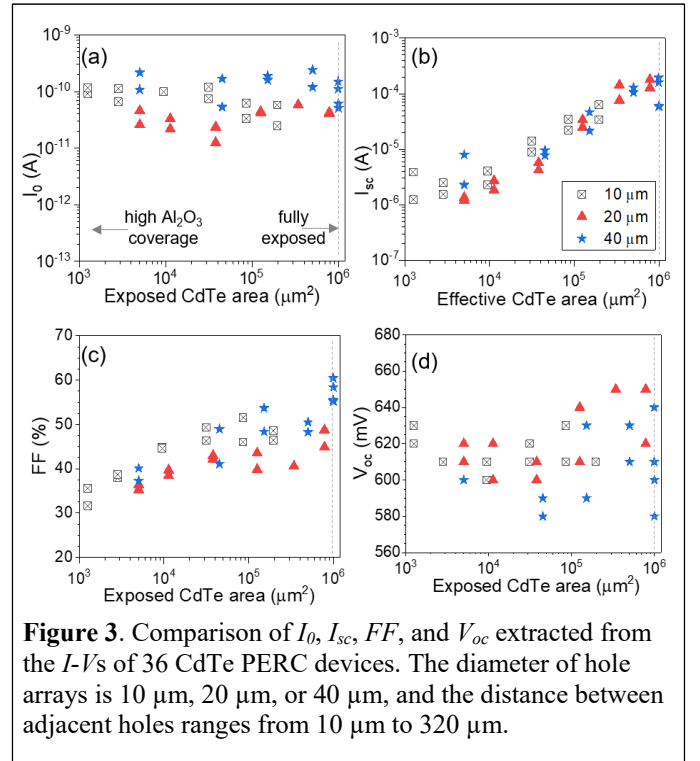
steel foil (40  $\mu\text{m}$ ) containing a square array (3  $\times$  4) with a spacing of 1 mm. This shadow mask was aligned to the hole array patterns on  $\text{Al}_2\text{O}_3/\text{CdTe}$  (top right in Figure 2). The sample was placed on a holder in an electron beam evaporator. Thin films of Cu/Au (3 nm/80 nm) were deposited on the patterned  $\text{Al}_2\text{O}_3/\text{CdTe}$  through the shadow mask, which served as a back contact. A front indium contact was formed on TCO after removing the CdTe segment using a razor blade. Figure 2 displays the complete CdTe PERC devices.

The dark and light current-voltage characteristics were measured using a probe station (dark enclosure) connected to a semiconductor analyzer (Agilent 4145C). Each probe tip (25  $\mu\text{m}$  diameter W-tip) was placed on top and bottom metal contact while recording the  $I$ - $V$ s using the LabVIEW program. Before the measurements, the solar simulator (G2V) was calibrated to 1-sun using a reference cell (Newport; 91150V).

### III. RESULTS AND DISCUSSION

We analyze the dark and light  $I$ - $V$ s measured from 36 CdTe PERC devices having various hole array patterns. All devices consisted of a patterned area in the center (1 mm  $\times$  1 mm) of the metal contact (2 mm  $\times$  2 mm). For a statistical comparison, we estimate the exposed CdTe area of each device from the design, where the Cu/Au metal is directly deposited on CdTe without the  $\text{Al}_2\text{O}_3$  layer. Figure 3 summarizes the parameters ( $I_0$ ,  $I_{sc}$ ,  $FF$ , and  $V_{oc}$ ) of CdTe PERC.

The distribution of leakage current of our devices (Figure 3a) is relatively constant, supporting the fidelity of the fabrication processes developed in this work. The magnitudes of  $I_{sc}$  and  $FF$



proportionally increase with the exposed CdTe area. As seen in Figure 3(b), the  $I_{sc}$  of the CdTe PERC having an exposed CdTe area of 1 % is 1  $\mu\text{A}$ . This current increases to 10 mA when the  $\text{Al}_2\text{O}_3$  layer is fully removed in the patterned area (1 mm  $\times$  1 mm). The  $FF$  increases to a factor of two (approximately 30 % to 60 %) with the  $\text{Al}_2\text{O}_3$  removal. These trends are expected as the electrically resistive  $\text{Al}_2\text{O}_3$  layer (20 nm thick) can interfere with the photocarrier collection (hole carriers) from CdTe to metal contact.

Interestingly, the  $V_{oc}$  trend (Figure 3d) for the As-doped CdTe PERC is notably different from that of  $I_{sc}$  and  $FF$ . The  $V_{oc}$  ranges from 580 mV to 660 mV, which seems independent to the exposed CdTe areas. In a close look, the  $V_{oc}$  slightly decreases from  $\approx 640$  mV to  $\approx 590$  mV when the CdTe area increases from  $10^3 \mu\text{m}^2$  (1 % of the total device area) to  $10^4 \mu\text{m}^2$  (10 %). The  $V_{oc}$  increases as high as 660 mV with the increase of the exposed CdTe area (40 %  $\sim$  80 %). The  $V_{oc}$  of the control devices, which have the fully open CdTe area (100 %), ranges from 580 mV to 640 mV, still below the highest  $V_{oc}$  observed with the patterned  $\text{Al}_2\text{O}_3$  PERC devices. We note that the  $V_{oc}$  trend of As-doped PERC is also significantly different from our Cu-doped CdTe PERC, where the  $V_{oc}$  decreases with the increased CdTe exposed area (not shown in the data). Our results indicate the electrically-active  $\text{Al}_2\text{O}_3$  patterns could play

an important role in determining the  $V_{oc}$  of advanced CdTe-based solar cells.

We have examined the performance of the As-doped CdTe PERC solar cells under heating. We annealed the complete PERC devices at 70  $^\circ\text{C}$  for 2.5 hours in this preliminary experiment. The diameter of the patterned  $\text{Al}_2\text{O}_3$  is 10  $\mu\text{m}$ , and the adjacent hole distance ranges from 10  $\mu\text{m}$  to 320  $\mu\text{m}$ . Figures 4 (a, b) shows the light  $I$ - $V$ s collected “before” and “after” the heating. Overall, the PERC devices preserve good diode behaviors after the heating.

Figures 4 (c  $\sim$  f) compare the device parameters of the saturation current ( $I_s$ ),  $I_{sc}$ ,  $FF$ , and  $V_{oc}$  extracted from the  $I$ - $V$ s. The magnitudes of the  $I_s$  and  $V_{oc}$  are relatively constant, while the  $I_{sc}$  and  $FF$  increase with the exposed CdTe area, with similar trends observed in Figure 3. The magnitudes of  $I_s$ ,  $I_{sc}$ , and  $FF$  show only slight variation after the heating at 70  $^\circ\text{C}$ . In contrast, the  $V_{oc}$  of the CdTe PERC increases after annealing with a magnitude as high as  $\approx 10$  % of its initial value (e.g., 600 mV to 650 mV). Presumably, the group-V dopant (As) in the CdTe bulk could be more activated, or the defects near  $\text{Al}_2\text{O}_3$  may be further passivated during the annealing [20]. Further studies are in progress to gain a better understanding of such heating effects and back-contact passivation.

#### IV. CONCLUSIONS

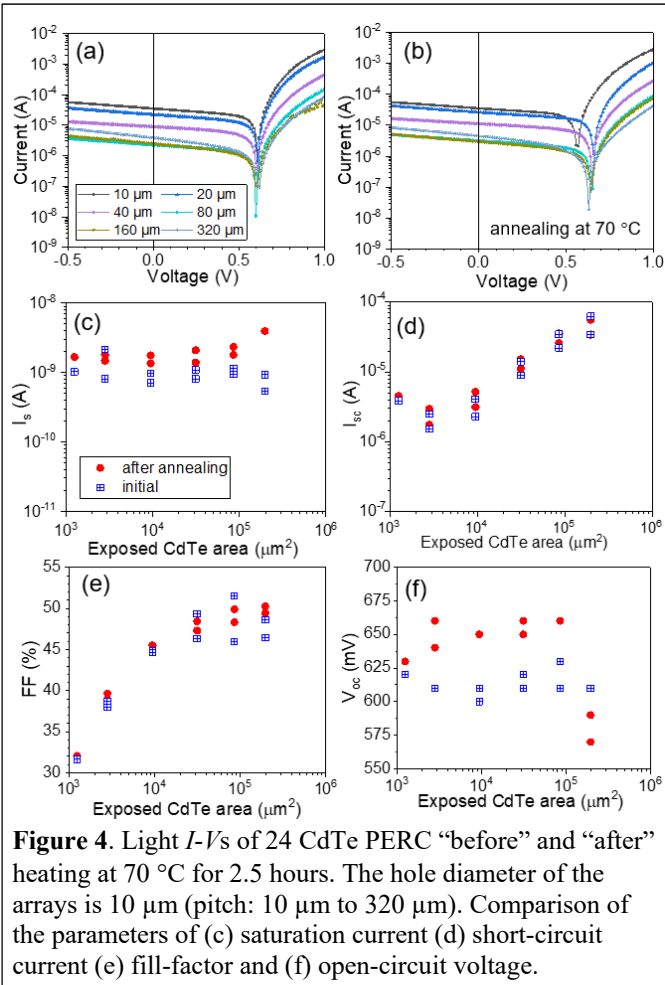
In summary, we have demonstrated the fabrication of CdTe PERC solar cells with a patterned  $\text{Al}_2\text{O}_3$  passivation layer. Our process based on laser-beam lithography enables reproducible patterning on a rough surface CdTe while maintaining the size of the array in the design. Quantitative analysis of the As-doped CdTe PERC shows a proportional increase of  $FF$  and  $J_{sc}$  with an exposed CdTe area. We have observed that the complete CdTe PERC annealing increases the  $V_{oc}$  by  $\approx 10$  % of their initial magnitudes, whereas the  $I_s$ ,  $I_{sc}$ , and  $FF$  show negligible changes. Our results indicate that the subsurface electronic properties of CdTe and the interplay between carrier selectivity and collection of the patterned  $\text{Al}_2\text{O}_3$  could be responsible for the observed PV characteristics.

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